

### 适用场景 Application

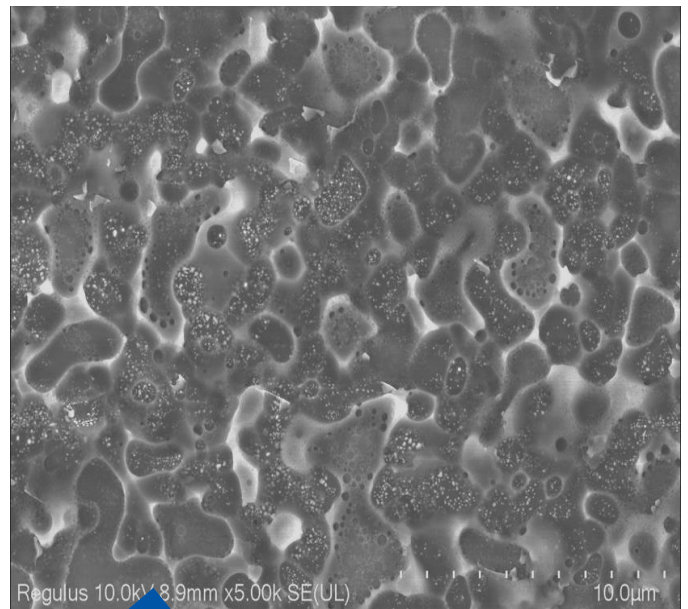
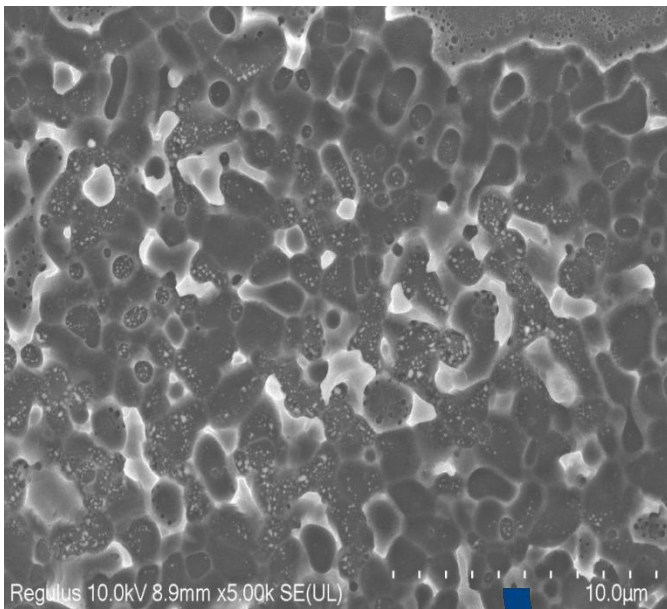
适用于 N 型硅片衬底的背接触结构，核心优势在于与 Poly 硅层形成优异的欧姆接触  
Applicable to back-contact structure of N-type silicon substrate, featuring superior ohmic contact with poly-Si layer.

### 印刷网版 Printing screen

适配 PI 无网结超细线网版、钢版等  
PI knotless screen with ultra fine line finger pattern

### 亮点 Highlight

- 精准活化Poly表面、生成银微晶接触点，构建低阻导电通道  
Precisely activate Poly surface to form silver microcrystal contacts and build low-resistance conductive paths.
- 烧结窗口宽、可靠性好，可有效提升电池转换效率与长期稳定性  
Broad firing window and excellent reliability, effectively improving cell conversion efficiency and long-term stability.
- 兼具优良的印刷流变性、适配 BC 电池细线化  
Combines excellent printing rheology and adapts to fine-line printing for BC cells.
- 低银耗降本，兼顾量产良率与经济性  
Low silver consumption reduces cost, balancing mass production yield and economic efficiency.



N 区优化无机配方，减薄界面玻璃层，降低接触电阻率，减少复合

Optimized inorganic formulation for N-region to thin the interfacial glass layer, reduce contact resistivity and minimize recombination.